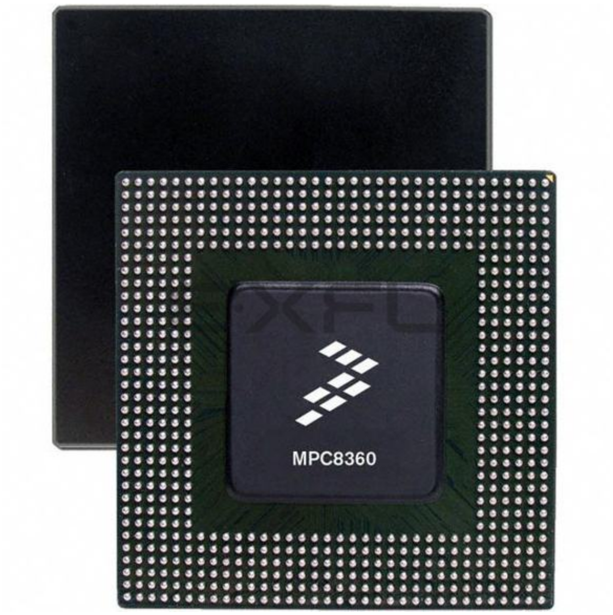
NXP USA Inc. - MPC8360ECVVAJDG Datasheet



Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	740-LBGA
Supplier Device Package	740-TBGA (37.5x37.5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8360ecvvajdg

This table provides the input AC timing specifications for the DDR SDRAM interface when GV_{DD}(typ) = 2.5 V.

Table 19. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.31	—	V	—

Table 20. DDR and DDR2 SDRAM Input AC Timing Specifications Mode

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
MDQS—MDQ/MECC input skew per byte	t_{DISKEW}			ps	1, 2
333 MHz		–750	750		
266 MHz		–1125	1125		
200 MHz		–1250	1250		

Notes:

1. AC timing values are based on the DDR data rate, which is twice the DDR memory bus frequency.
2. Maximum possible skew between a data strobe (MDQS[n]) and any corresponding bit of data (MDQ[8n + {0...7}] if $0 \le n \le 7$) or ECC (MECC[{0...7}] if n = 8).

This figure shows the input timing diagram for the DDR controller.

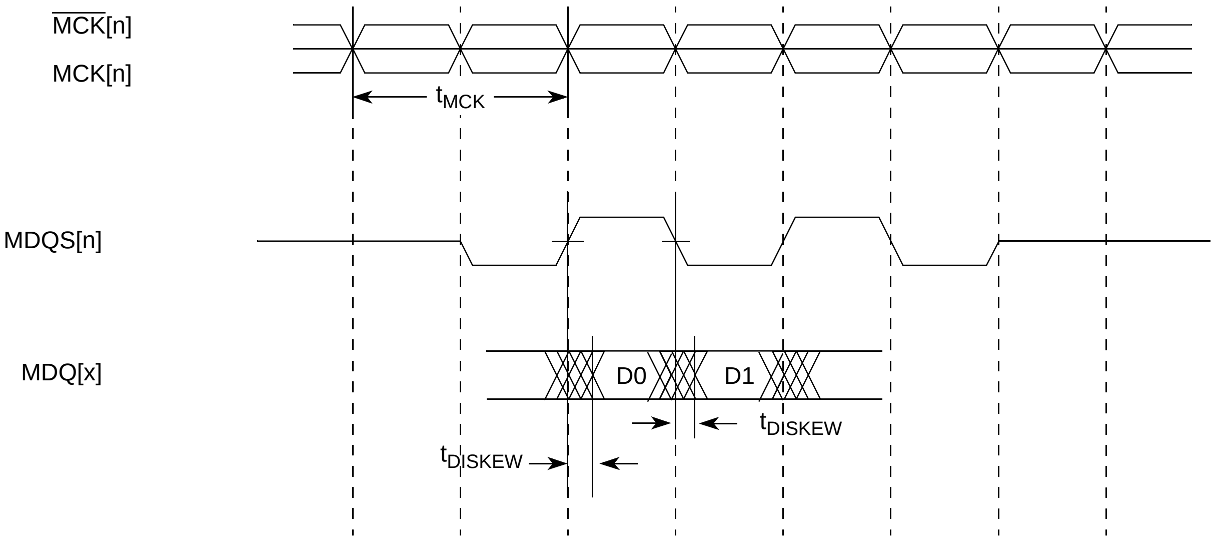


Figure 6. DDR Input Timing Diagram

Physical Layer Device Specification Version 1.2a (9/22/2000). The electrical characteristics for the MDIO and MDC are specified in Section 8.3, “Ethernet Management Interface Electrical Characteristics.”

8.1.1 10/100/1000 Ethernet DC Electrical Characteristics

The electrical characteristics specified here apply to media independent interface (MII), reduced gigabit media independent interface (RGMII), reduced ten-bit interface (RTBI), reduced media independent interface (RMII) signals, management data input/output (MDIO) and management data clock (MDC).

The MII and RMII interfaces are defined for 3.3 V, while the RGMII and RTBI interfaces can be operated at 2.5 V. The RGMII and RTBI interfaces follow the *Reduced Gigabit Media-Independent Interface (RGMII) Specification Version 1.3*. The RMII interface follows the *RMII Consortium RMII Specification Version 1.2*.

Table 25. RGMII/RTBI, GMII, TBI, MII, and RMII DC Electrical Characteristics (when operating at 3.3 V)

Parameter	Symbol	Conditions		Min	Max	Unit	Notes
Supply voltage 3.3 V	LV_{DD}	—		2.97	3.63	V	1
Output high voltage	V_{OH}	I_{OH} = –4.0 mA	LV_{DD} = Min	2.40	LV_{DD} + 0.3	V	—
Output low voltage	V_{OL}	I_{OL} = 4.0 mA	LV_{DD} = Min	GND	0.50	V	—
Input high voltage	V_{IH}	—	—	2.0	LV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	—	—	–0.3	0.90	V	—
Input current	I_{IN}	0 V ≤V_{IN} ≤LV_{DD}		—	±10	μA	—

Note:

1. GMII/MII pins that are not needed for RGMII, RMII, or RTBI operation are powered by the OV_{DD} supply.

Table 26. RGMII/RTBI DC Electrical Characteristics (when operating at 2.5 V)

Parameters	Symbol	Conditions		Min	Max	Unit
Supply voltage 2.5 V	LV_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.00	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND – 0.3	0.40	V
Input high voltage	V_{IH}	—	LV_{DD} = Min	1.7	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	LV_{DD} = Min	–0.3	0.70	V
Input current	I_{IN}	0 V ≤V_{IN} ≤LV_{DD}		—	±10	μA

8.2 GMII, MII, RMII, TBI, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for GMII, MII, TBI, RGMII, and RTBI are presented in this section.

8.2.1 GMII Timing Specifications

This sections describe the GMII transmit and receive AC timing specifications.

8.2.1.1 GMII Transmit AC Timing Specifications

This table provides the GMII transmit AC timing specifications.

Table 27. GMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
GTX_CLK clock period	t_{GTX}	—	8.0	—	ns	—
GTX_CLK duty cycle	$t_{GTXH/tGTX}$	40	—	60	%	—
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	t_{GTKHDX} t_{GTKHDV}	0.5 —	—	— 5.0	ns	3
GTX_CLK clock rise time, (20% to 80%)	t_{GTXR}	—	—	1.0	ns	—
GTX_CLK clock fall time, (80% to 20%)	t_{GTXF}	—	—	1.0	ns	—
GTX_CLK125 clock period	t_{G125}	—	8.0	—	ns	2
GTX_CLK125 reference clock duty cycle measured at $LV_{DD/2}$	t_{G125H}/t_{G125}	45	—	55	%	2

Notes:

1. The symbols used for timing specifications follow the pattern $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This symbol is used to represent the external GTX_CLK125 signal and does not follow the original symbol naming convention.
3. In rev. 2.0 silicon, due to errata, t_{GTKHDX} minimum and t_{GTKHDV} maximum are not supported when the GTX_CLK is selected. Refer to Errata *QE_ENET18* in *Chip Errata for the MPC8360E, Rev. 1*.

This figure shows the GMII transmit AC timing diagram.

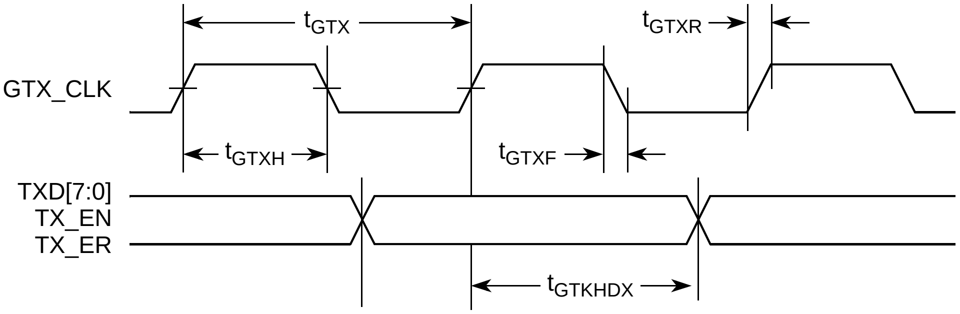


Figure 10. GMII Transmit AC Timing Diagram

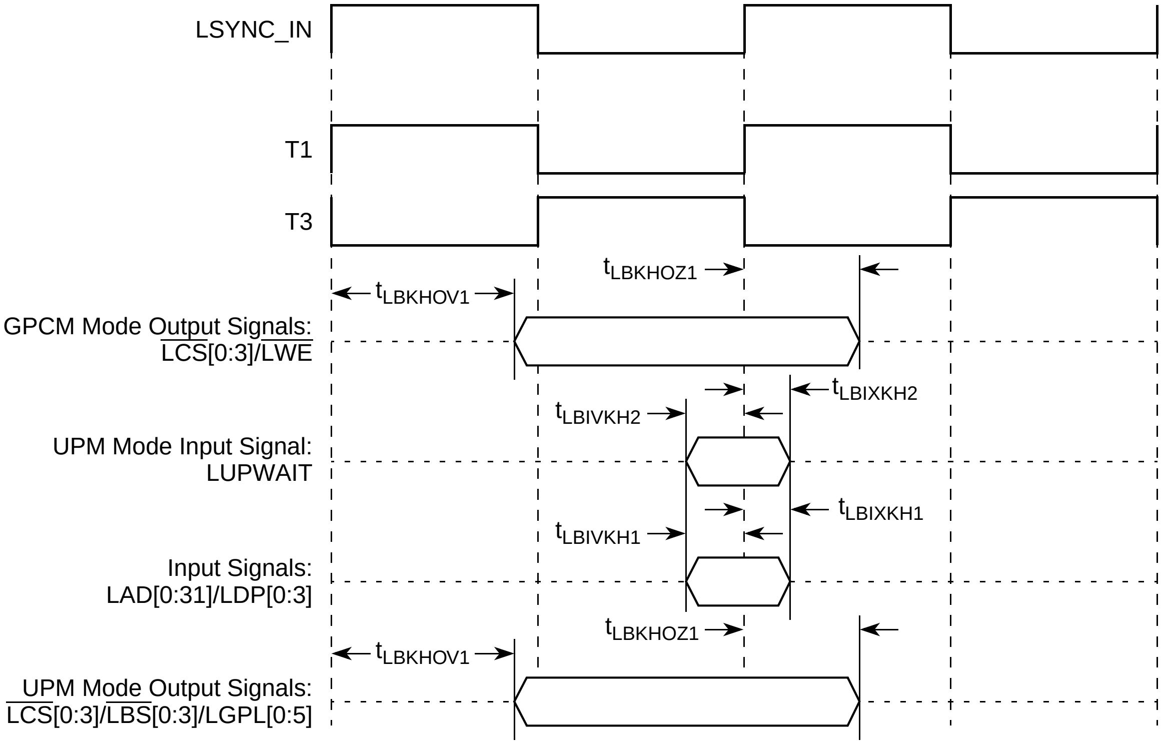


Figure 25. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Enabled)

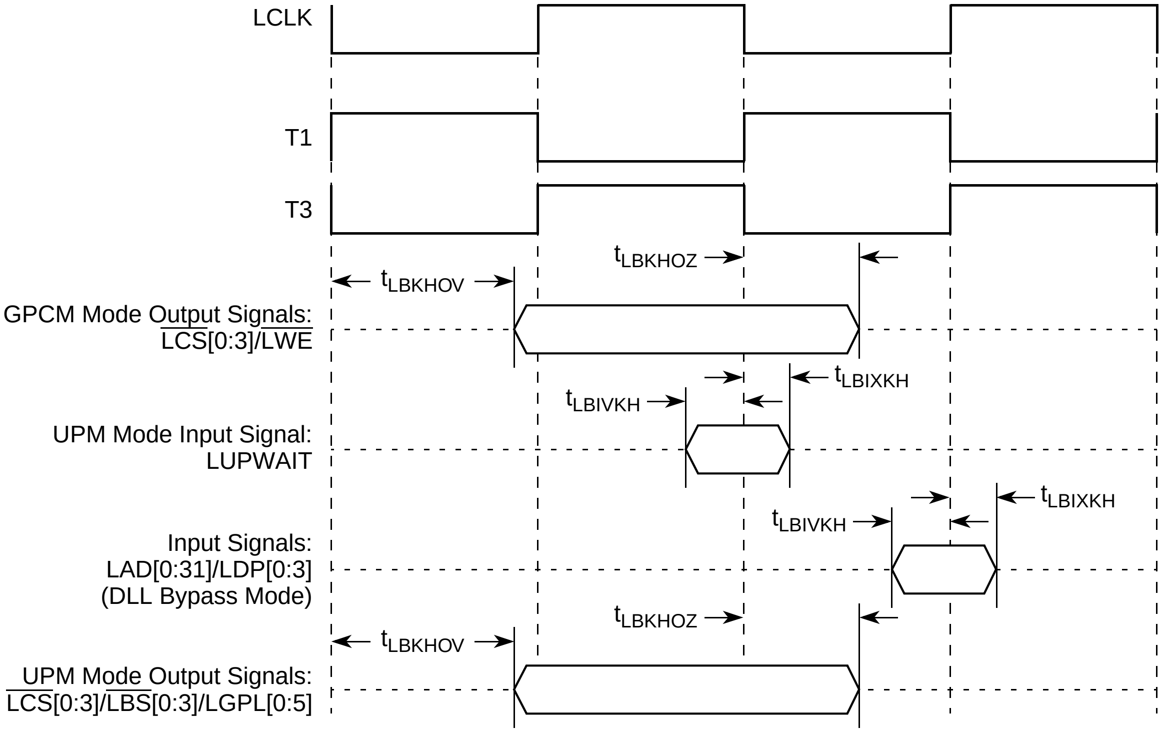


Figure 26. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Bypass Mode)

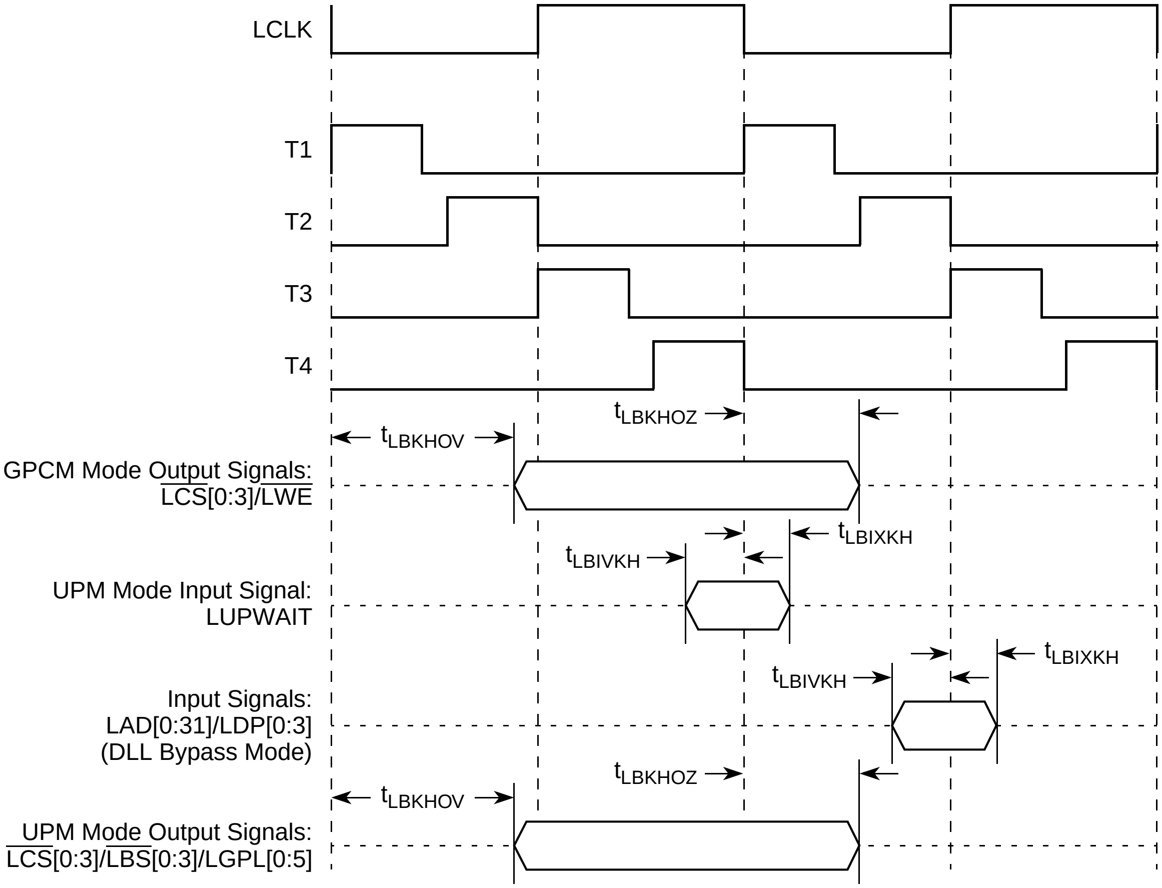


Figure 27. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4 (DLL Bypass Mode)

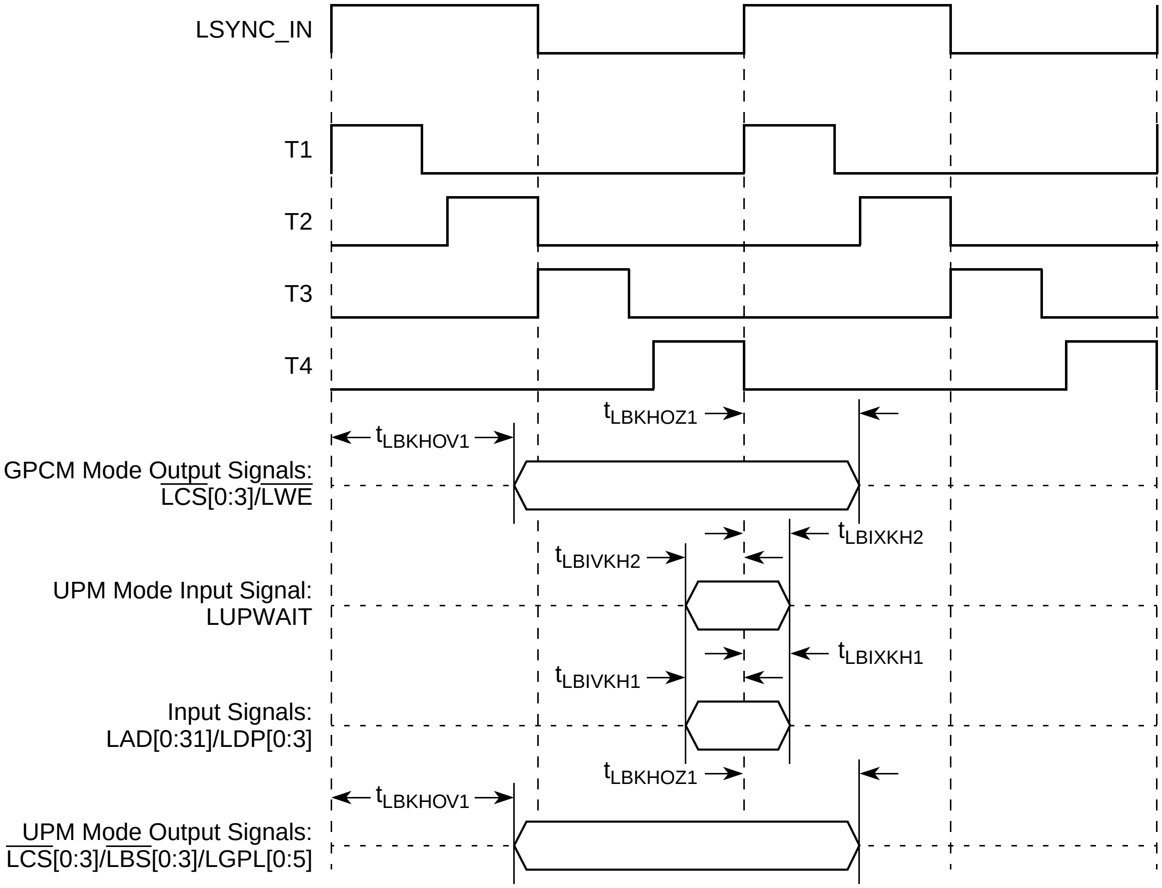


Figure 28. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4 (DLL Enabled)

10 JTAG

This section describes the DC and AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the MPC8360E/58E.

10.1 JTAG DC Electrical Characteristics

This table provides the DC electrical characteristics for the IEEE 1149.1 (JTAG) interface of the device.

Table 42. JTAG interface DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.5	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤V_{IN} ≤OV_{DD}	—	±10	μA

10.2 JTAG AC Electrical Characteristics

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device.

This table provides the JTAG AC timing specifications as defined in Figure 30 through Figure 33.

Table 43. JTAG AC Timing Specifications (Independent of CLKIN)[1]

At recommended operating conditions (see Table 2).

Parameter	Symbol [2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock duty cycle	t_{JTKHKL}/t_{JTG}	45	55	%	—
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	—
$\overline{\text{TRST}}$ assert time	t_{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	 t_{JTDVKH} t_{JTIVKH}	 4 4	 — —	ns	4
Input hold times: Boundary-scan data TMS, TDI	 t_{JTDXKH} t_{JTIXKH}	 10 10	 — —	ns	4
Valid times: Boundary-scan data TDO	 t_{JTKLDV} t_{JTKLOV}	 2 2	 11 11	ns	5
Output hold times: Boundary-scan data TDO	 t_{JTKLDX} t_{JTKLOX}	 2 2	 — —	ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 2 2	 19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 22). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design and characterization.

This figure provides the AC test load for TDO and the boundary-scan outputs of the device.

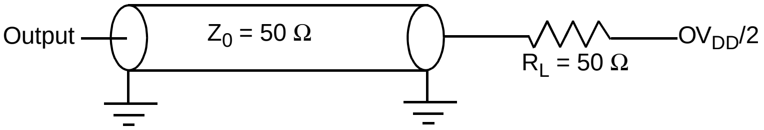
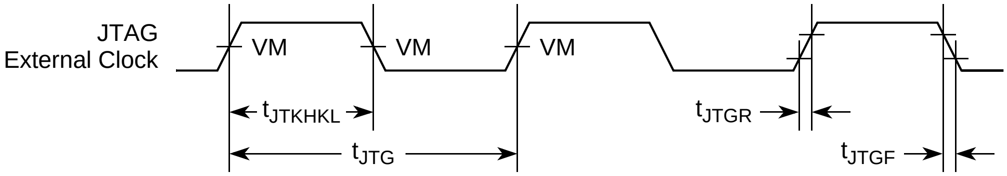


Figure 29. AC Test Load for the JTAG Interface

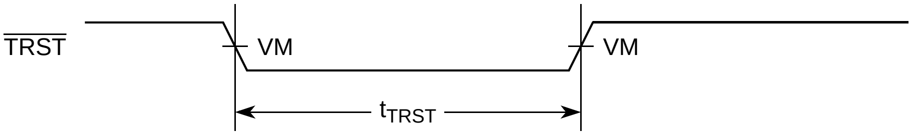
This figure provides the JTAG clock input timing diagram.



VM = Midpoint Voltage ($OV_{DD}/2$)

Figure 30. JTAG Clock Input Timing Diagram

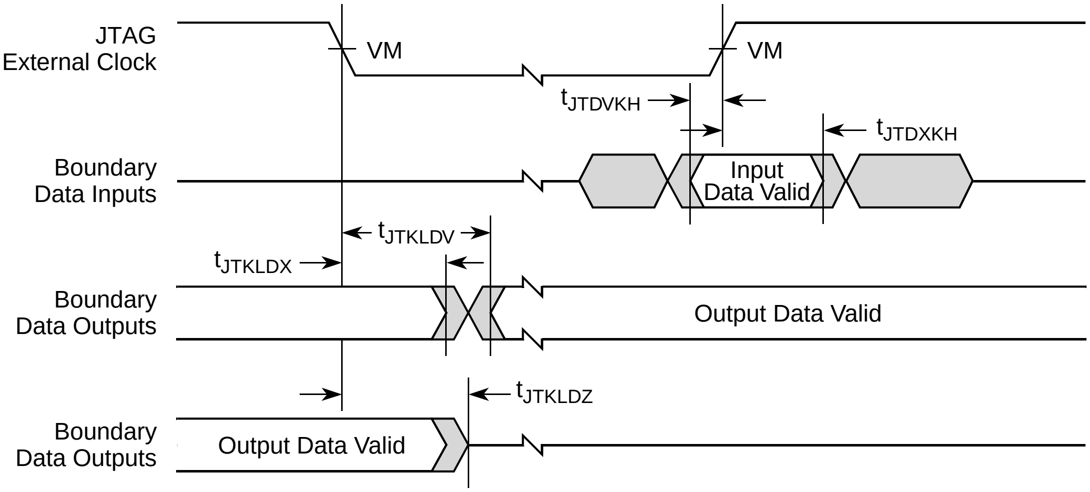
This figure provides the $\overline{\text{TRST}}$ timing diagram.



VM = Midpoint Voltage ($OV_{DD}/2$)

Figure 31. $\overline{\text{TRST}}$ Timing Diagram

This figure provides the boundary-scan timing diagram.



VM = Midpoint Voltage ($OV_{DD}/2$)

Figure 32. Boundary-Scan Timing Diagram

11.2 I^{2}C AC Electrical Specifications

This table provides the AC timing parameters for the I^{2}C interface of the device.

Table 45. I^{2}C AC Electrical Specifications

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 44).

Parameter	Symbol[1]	Min	Max	Unit	Note
SCL clock frequency	f_{I2C}	0	400	kHz	2
Low period of the SCL clock	t_{I2CL}	1.3	—	µs	—
High period of the SCL clock	t_{I2CH}	0.6	—	µs	—
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	µs	—
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	µs	—
Data setup time	t_{I2DVKH}	100	—	ns	3
Data hold time: CBUS compatible masters I^{2}C bus devices	t_{I2DXKL}	 — 0[2]	 — 0.9[3]	µs	—
Rise time of both SDA and SCL signals	t_{I2CR}	20 + 0.1 C_b[4]	300	ns	—
Fall time of both SDA and SCL signals	t_{I2CF}	20 + 0.1 C_b[4]	300	ns	—
Set-up time for STOP condition	t_{I2PVKH}	0.6	—	µs	—
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	µs	—
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	$0.1 \times OV_{DD}$	—	V	—
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	$0.2 \times OV_{DD}$	—	V	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{I2DVKH} symbolizes I^{2}C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I^{2}C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I^{2}C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. The device provides a hold time of at least 300 ns for the SDA signal (referred to the V_{IH} min of the SCL signal) to bridge the undefined region of the falling edge of SCL.
3. The maximum t_{I2DVKH} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. C_B = capacitance of one bus line in pF.

This figure provides the AC test load for the I^2C.

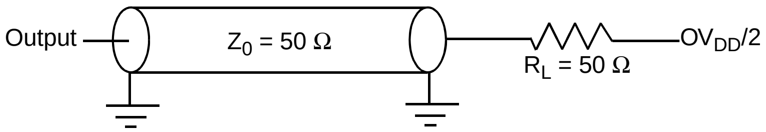


Figure 34. I^2C AC Test Load

This figure shows the AC timing diagram for the I^2C bus.

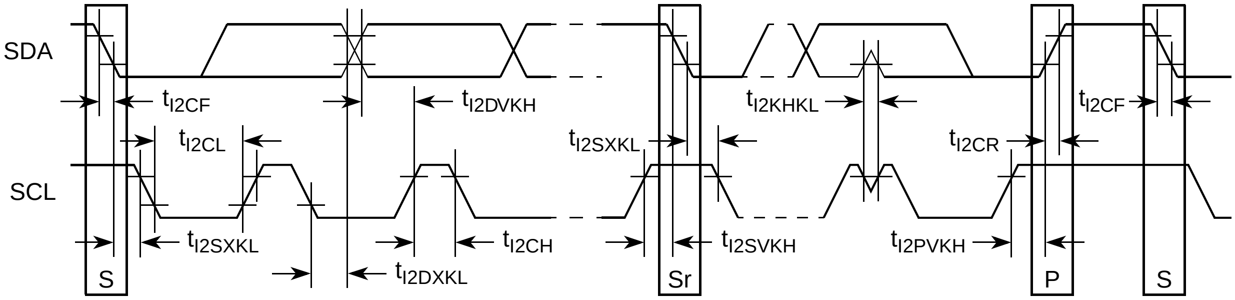


Figure 35. I^2C Bus AC Timing Diagram

12 PCI

This section describes the DC and AC electrical specifications for the PCI bus of the MPC8360E/58E.

12.1 PCI DC Electrical Characteristics

This table provides the DC electrical characteristics for the PCI interface of the device.

Table 46. PCI DC Electrical Characteristics

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V_{IH}	$V_{OUT} \geq V_{OH}$ (min) or $V_{OUT} \leq V_{OL}$ (max)	$0.5 \times OV_{DD}$	$OV_{DD} + 0.5$	V
Low-level input voltage	V_{IL}		-0.5	$0.3 \times OV_{DD}$	V
High-level output voltage	V_{OH}	$I_{OH} = -500\ \mu A$	$0.9 \times OV_{DD}$	—	V
Low-level output voltage	V_{OL}	$I_{OL} = 1500\ \mu A$	—	$0.1 \times OV_{DD}$	V
Input current	I_{IN}	$0\ V \leq V_{IN}^1 \leq OV_{DD}$	—	±10	μA

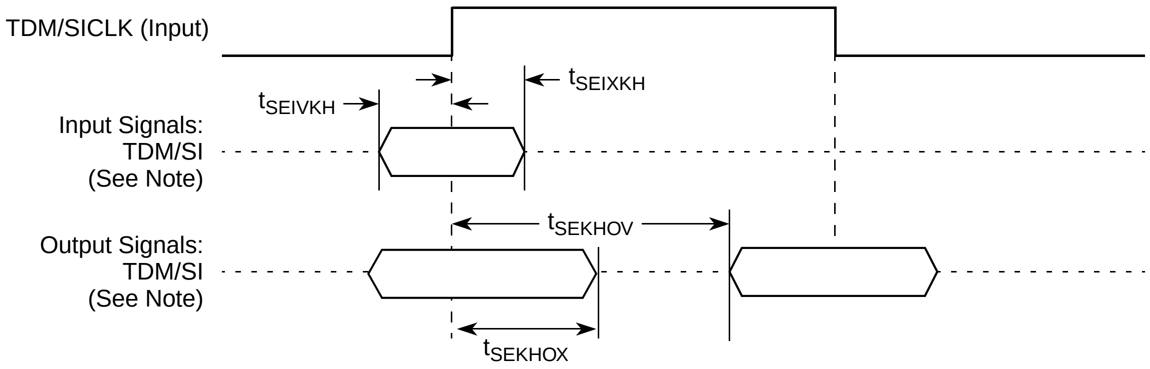
12.2 PCI AC Electrical Specifications

This section describes the general AC timing parameters of the PCI bus of the device. Note that the PCI_CLK or PCI_SYNC_IN signal is used as the PCI input clock depending on whether the device is configured as a host or agent device. This table provides the PCI AC timing specifications at 66 MHz.

Table 47. PCI AC Timing Specifications at 66 MHz

Parameter	Symbol[1]	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	6.0	ns	2, 5
Output hold from clock	t_{PCKHOX}	1	—	ns	2

This figure shows the TDM/SI timing with external clock.



Note: The clock edge is selectable on TDM/SI

Figure 45. TDM/SI AC Timing (External Clock) Diagram

17.3 UTOPIA/POS

This section describes the DC and AC electrical specifications for the UTOPIA/POS of the MPC8360E/58E.

17.4 UTOPIA/POS DC Electrical Characteristics

This table provides the DC electrical characteristics for the device UTOPIA.

Table 59. UTOPIA DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = –8.0$ mA	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 8.0$ mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V $\leq V_{IN} \leq OV_{DD}$	—	±10	μA

17.5 UTOPIA/POS AC Timing Specifications

This table provides the UTOPIA input and output AC timing specifications.

Table 60. UTOPIA AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit	Notes
UTOPIA outputs—Internal clock delay	t_{UIKHOV}	0	11.5	ns	—
UTOPIA outputs—External clock delay	t_{UEKHOV}	1	11.6	ns	—
UTOPIA outputs—Internal clock high impedance	t_{UIKHOX}	0	8.0	ns	—
UTOPIA outputs—External clock high impedance	t_{UEKHOX}	1	10.0	ns	—
UTOPIA inputs—Internal clock input setup time	t_{UIIVKH}	6	—	ns	—
UTOPIA inputs—External clock input setup time	t_{UEIVKH}	4	—	ns	3

Table 62. HDLC, BISYNC, and Transparent AC Timing Specifications[1] (continued)

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock high impedance	t_{HIKHOX}	-0.5	5.5	ns
Outputs—External clock high impedance	t_{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t_{HIIVKH}	8.5	—	ns
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t_{HIIXKH}	1.4	—	ns
Inputs—External clock input hold time	t_{HEIXKH}	1	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Table 63. Synchronous UART AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock delay	$t_{UAIKHOV}$	0	11.3	ns
Outputs—External clock delay	$t_{UAEKHOV}$	1	14	ns
Outputs—Internal clock high impedance	$t_{UAIKHOX}$	0	11	ns
Outputs—External clock high impedance	$t_{UAEKHOX}$	1	14	ns
Inputs—Internal clock input setup time	$t_{UAIIVKH}$	6	—	ns
Inputs—External clock input setup time	$t_{UAEIVKH}$	8	—	ns
Inputs—Internal clock input hold time	$t_{UAIIXKH}$	1	—	ns
Inputs—External clock input hold time	$t_{UAEIXKH}$	1	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

This figure provides the AC test load.

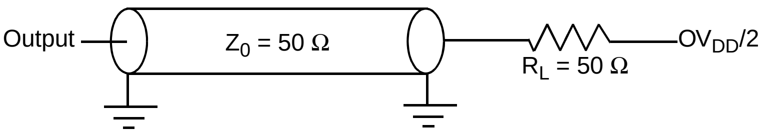


Figure 49. AC Test Load

20 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8360E/58E is available in a tape ball grid array (TBGA), see Section 20.1, “Package Parameters for the TBGA Package,” and Section 20.2, “Mechanical Dimensions of the TBGA Package,” for information on the package.

20.1 Package Parameters for the TBGA Package

The package parameters for rev. 2.0 silicon are as provided in the following list. The package type is 37.5 mm × 37.5 mm, 740 tape ball grid array (TBGA).

Package outline	37.5 mm × 37.5 mm
Interconnects	740
Pitch	1.00 mm
Module height (typical)	1.46 mm
Solder Balls	62 Sn/36 Pb/2 Ag (ZU package) 95.5 Sn/0.5 Cu/4Ag (VV package)
Ball diameter (typical)	0.64 mm

20.2 Mechanical Dimensions of the TBGA Package

This figure depicts the mechanical dimensions and bottom surface nomenclature of the device, 740-TBGA package.

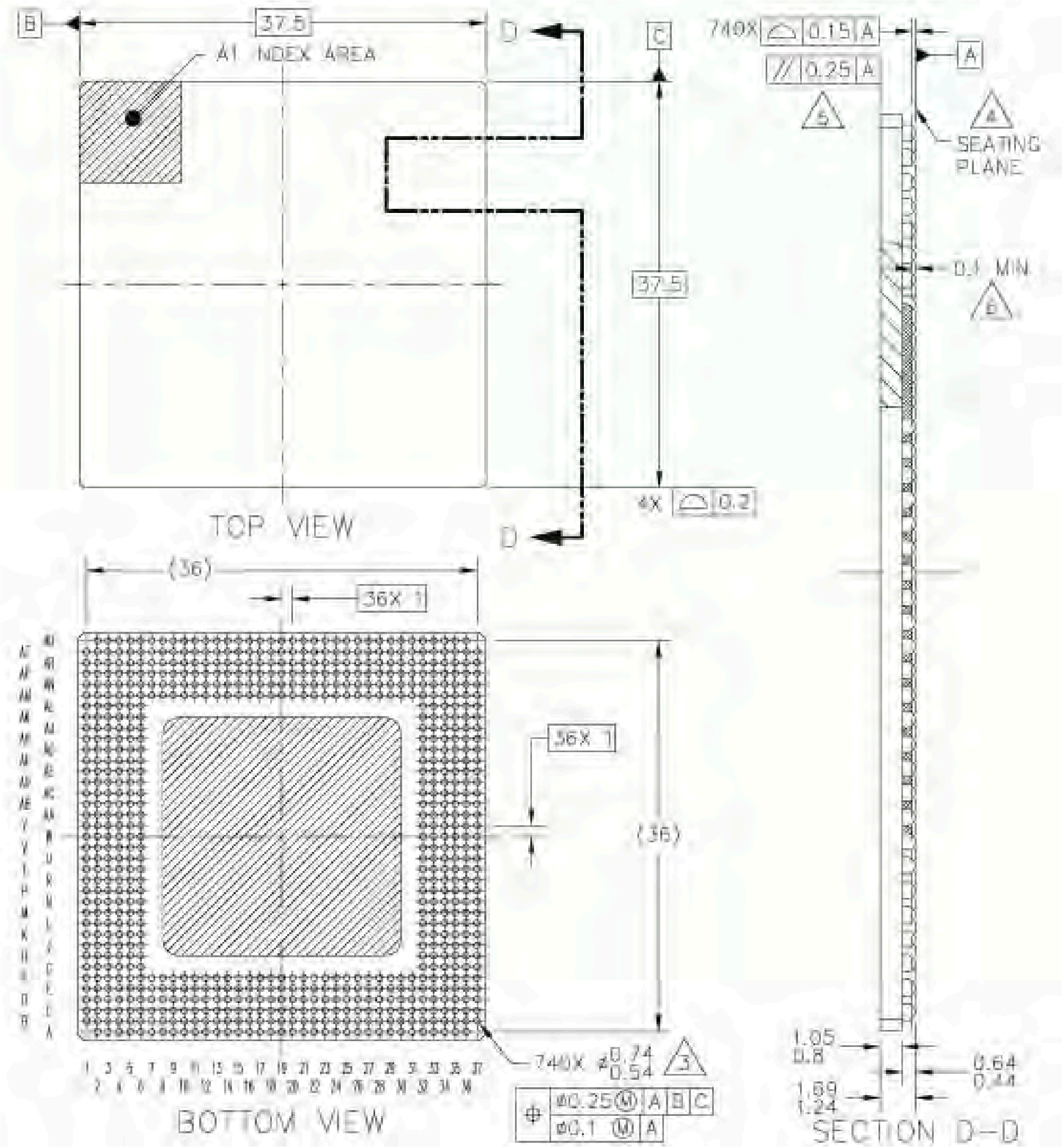


Figure 53. Mechanical Dimensions and Bottom Surface Nomenclature of the TBGA Package

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$LV_{DD}1$	C17, D16	Power for UCC2 Ethernet interface option 1 (2.5 V, 3.3 V)	$LV_{DD}1$	9
$LV_{DD}2$	B18, E21	Power for UCC2 Ethernet interface option 2 (2.5 V, 3.3 V)	$LV_{DD}2$	9
V_{DD}	C36, D29, D35, E16, F9, F12, F15, F17, F18, F20, F21, F23, F25, F26, F29, F31, F32, F33, G6, J6, K32, M32, N6, P33, R6, R32, U32, V6, Y5, Y32, AB6, AB33, AD6, AF32, AK6, AL6, AM7, AM9, AM10, AM11, AM12, AM13, AM14, AM15, AM18, AM21, AM25, AM28, AM32, AN15, AN21, AN26, AU9, AU17	Power for core (1.2 V)	V_{DD}	—
OV_{DD}	A10, B9, B15, B32, C1, C12, C22, C29, D24, E3, E10, E27, G4, H35, J1, J35, K2, M4, N3, N34, R2, R37, T36, U2, U33, V4, V34, W3, Y35, Y37, AA1, AA36, AB2, AB34	PCI, 10/100 Ethernet, and other standard (3.3 V)	OV_{DD}	—
MVREF1	AN20	I	DDR reference voltage	—
MVREF2	AU32	I	DDR reference voltage	—
SPARE1	B11	I/O	OV_{DD}	8
SPARE3	AH32	—	GV_{DD}	8
SPARE4	AU18	—	GV_{DD}	7
SPARE5	AP1	—	GV_{DD}	8

Table 72. CSB Frequency Options (continued)

CFG_CLKIN_DIV at Reset[1]	**SPMF**	***csb_clk*: Input Clock Ratio**[2]	**Input Clock Frequency (MHz)**[2]			
			16.67	**25**	**33.33**	**66.67**
			***csb_clk* Frequency (MHz)**			
Low	0110	6:1	100	150	200	
Low	0111	7:1	116	175	233	
Low	1000	8:1	133	200	266	
Low	1001	9:1	150	225	300	
Low	1010	10:1	166	250	333	
Low	1011	11:1	183	275		
Low	1100	12:1	200	300		
Low	1101	13:1	216	325		
Low	1110	14:1	233			
Low	1111	15:1	250			
Low	0000	16:1	266			
High	0010	2:1				133
High	0011	3:1			100	200
High	0100	4:1			133	266
High	0101	5:1			166	333
High	0110	6:1			200	
High	0111	7:1			233	
High	1000	8:1				
High	1001	9:1				
High	1010	10:1				
High	1011	11:1				
High	1100	12:1				
High	1101	13:1				
High	1110	14:1				
High	1111	15:1				
High	0000	16:1				

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[1] CFG_CLKIN_DIV is only used for host mode; CLKIN must be tied low and CFG_CLKIN_DIV must be pulled down (low) in agent mode.

[2] CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

21.3 QUICC Engine Block PLL Configuration

The QUICC Engine block PLL is controlled by the RCWL[CEPMF], RCWL[CEPDF], and RCWL[CEVCOD] parameters. This table shows the multiplication factor encodings for the QUICC Engine block PLL.

Table 74. QUICC Engine Block PLL Multiplication Factors

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF])
00000	0	× 16
00001	0	Reserved
00010	0	× 2
00011	0	× 3
00100	0	× 4
00101	0	× 5
00110	0	× 6
00111	0	× 7
01000	0	× 8
01001	0	× 9
01010	0	× 10
01011	0	× 11
01100	0	× 12
01101	0	× 13
01110	0	× 14
01111	0	× 15
10000	0	× 16
10001	0	× 17
10010	0	× 18
10011	0	× 19
10100	0	× 20
10101	0	× 21
10110	0	× 22
10111	0	× 23
11000	0	× 24
11001	0	× 25
11010	0	× 26
11011	0	× 27
11100	0	× 28

$$T_J = T_B + (R_{\theta JB} \times P_D)$$

where:

T_J = junction temperature (° C)
T_B = board temperature at the package perimeter (° C)
$R_{\theta JA}$ = junction to board thermal resistance (° C/W) per JESD51-8
P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

22.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, the Thermal Characterization Parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

T_J = junction temperature (° C)
T_T = thermocouple temperature on top of package (° C)
Ψ_{JT} = junction-to-ambient thermal resistance (° C/W)
P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

22.2.4 Heat Sinks and Junction-to-Ambient Thermal Resistance

In some application environments, a heat sink is required to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction to case thermal resistance and a case to ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

where:

$R_{\theta JA}$ = junction-to-ambient thermal resistance (° C/W)
$R_{\theta JC}$ = junction-to-case thermal resistance (° C/W)
$R_{\theta CA}$ = case-to-ambient thermal resistance (° C/W)

$R_{\theta JC}$ is device related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the airflow around the device, the interface material, the mounting arrangement on printed-circuit board, or change the thermal dissipation on the printed-circuit board surrounding the device.

To illustrate the thermal performance of the devices with heat sinks, the thermal performance has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, airflow, adjacent component power dissipation) and the physical space available. Because there is not a standard application environment, a standard heat sink is not required.

This table shows heat sinks and junction-to-ambient thermal resistance for TBGA package.

Table 78. Heat Sinks and Junction-to-Ambient Thermal Resistance of TBGA Package

Heat Sink Assuming Thermal Grease	Airflow	35 × 35 mm TBGA
		Junction-to-Ambient Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convention	10.7
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	6.2
AAVID 30 × 30 × 9.4 mm pin fin	2 m/s	5.3
AAVID 31 × 35 × 23 mm pin fin	Natural convention	8.1
AAVID 31 × 35 × 23 mm pin fin	1 m/s	4.4
AAVID 31 × 35 × 23 mm pin fin	2 m/s	3.7
Wakefield, 53 × 53 × 25 mm pin fin	Natural convention	5.4
Wakefield, 53 × 53 × 25 mm pin fin	1 m/s	3.2
Wakefield, 53 × 53 × 25 mm pin fin	2 m/s	2.4
MEI, 75 × 85 × 12 no adjacent board, extrusion	Natural convention	6.4
MEI, 75 × 85 × 12 no adjacent board, extrusion	1 m/s	3.8
MEI, 75 × 85 × 12 no adjacent board, extrusion	2 m/s	2.5
MEI, 75 × 85 × 12 mm, adjacent board, 40 mm side bypass	1 m/s	2.8

Accurate thermal design requires thermal modeling of the application environment using computational fluid dynamics software which can model both the conduction cooling and the convection cooling of the air moving through the application. Simplified thermal models of the packages can be assembled using the junction-to-case and junction-to-board thermal resistances listed in the thermal resistance table. More detailed thermal models can be made available on request.

Heat sink vendors include the following:

Aavid Thermalloy 80 Commercial St. Concord, NH 03301 Internet: www.aavidthermalloy.com	603-224-9988
Alpha Novatech 473 Sapena Ct. #15 Santa Clara, CA 95054 Internet: www.alphanovatech.com	408-749-7601
International Electronic Research Corporation (IERC) 413 North Moss St. Burbank, CA 91502 Internet: www.ctscorp.com	818-842-7277

23.7 Pull-Up Resistor Requirements

The device requires high resistance pull-up resistors (10 kΩ is recommended) on open drain type pins including I^2C pins, Ethernet Management MDIO pin, and EPIC interrupt pins.

For more information on required pull-up resistors and the connections required for the JTAG interface, see *MPC8360E/MPC8358E PowerQUICC Design Checklist* (AN3097).

24 Ordering Information

24.1 Part Numbers Fully Addressed by this Document

This table provides the Freescale part numbering nomenclature for the MPC8360E/58E. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. Additionally to the processor frequency, the part numbering scheme also includes an application modifier, which may specify special application conditions. Each part number also contains a revision code that refers to the die mask revision number.

Table 80. Part Numbering Nomenclature[1]

MPC	***nnnn***	***e***	***t***	***pp***	***aa***	***a***	***a***	***A***
Product Code	**Part Identifier**	**Encryption Acceleration**	**Temperature Range**	**Package**[2]	**Processor Frequency**[3]	**Platform Frequency**	**QUICC Engine Frequency**	**Die Revision**
MPC	8358	Blank = not included E = included	Blank = 0° C T_A to 105° C T_J C= –40° C T_A to 105° C T_J	ZU = TBGA VV = TBGA (no lead)	e300 core speed AD = 266 MHz AG = 400 MHz	D = 266 MHz	E = 300 MHz G = 400 MHz	A = rev. 2.1 silicon
	8360				e300 core speed AG = 400 MHz AJ = 533 MHz AL = 667 MHz	D = 266 MHz F = 333 MHz	G = 400 MHz H = 500 MHz	A = rev. 2.1 silicon
MPC (rev. 2.0 silicon only)	8360	Blank = not included E = included	0° C T_A to 70° C T_J	ZU = TBGA VV = TBGA (no lead)	e300 core speed AH = 500 MHz AL = 667 MHz	F = 333 MHz	G = 400 MHz H = 500 MHz	—

Notes:

1. Not all processor, platform, and QUICC Engine block frequency combinations are supported. For available frequency combinations, contact your local Freescale sales office or authorized distributor.
2. See Section 20, “Package and Pin Listings,” for more information on available package types.
3. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.

This table shows the SVR settings by device and package type.

Table 81. SVR Settings

Device	**Package**	**SVR (Rev. 2.0)**	**SVR (Rev. 2.1)**
MPC8360E	TBGA	0x8048_0020	0x8048_0021
MPC8360	TBGA	0x8049_0020	0x8049_0021